SEMICONDUCTOR STRUCTURE WITH SMOOTHED SURFACE AND PROCESS FOR OBTAINING SUCH A STRUCTURE

ABSTRACT

The present invention relates to a process for smoothing the surface of a semiconductor wafer, comprising the fusing of the said surface by scanning the said surface with a fusion beam, characterized in that it comprises:

- The definition of a reference length,
- The adjustment of the parameters of the fusion beam so as to fuse, during the scanning of the surface, a local surface zone of the wafer whose length is greater than or equal to the reference length,
- The fusion thus carried out making it possible to smooth the said surface so as to eliminate the surface roughnesses of period lower than the reference length.

The present invention also relates to a semiconductor wafer comprising a surface layer made of a semiconducting material for this purpose.

Fig 2b.